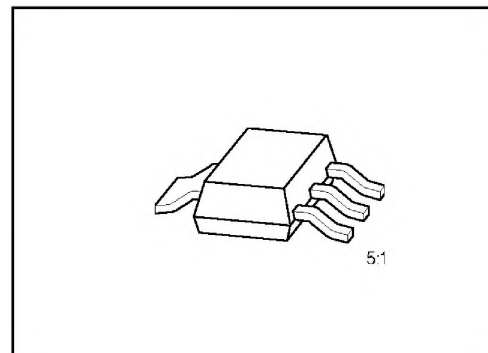


## PNP Silicon High-Voltage Transistors

**PZTA 92**  
**PZTA 93**

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary types: PZTA 42, PZTA 43 (NPN)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration				Package <sup>1)</sup>
			1	2	3	4	
PZTA 92	PZTA 92	Q62702-Z2037	B	C	E	C	SOT-223
PZTA 93	PZTA 93	Q62702-Z2038					

### Maximum Ratings

Parameter	Symbol	Values		Unit
		PZTA 92	PZTA 93	
Collector-emitter voltage	$V_{CE0}$	300	200	V
Collector-base voltage	$V_{CB0}$	300	200	
Emitter-base voltage	$V_{EB0}$	5		
Collector current	$I_C$	500		mA
Base current	$I_B$	100		
Total power dissipation, $T_s = 124\text{ °C}$	$P_{tot}$	1.5		W
Junction temperature	$T_j$	150		°C
Storage temperature range	$T_{stg}$	- 65 ... + 150		

### Thermal Resistance

Junction - ambient <sup>2)</sup>	$R_{th\ JA}$	≤ 72	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 17	

1) For detailed information see chapter Package Outlines.

2) Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm<sup>2</sup> Cu.

## Electrical Characteristics

at  $T_A = 25\text{ °C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

### DC characteristics

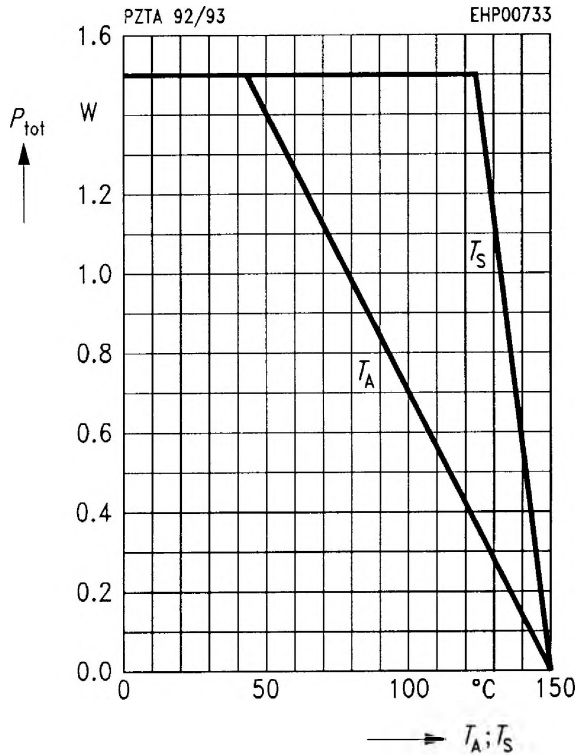
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CE0}$	300	–	–	V	
PZTA 92		–	–	–		
PZTA 93		200	–	–		
Collector-base breakdown voltage $I_C = 100\text{ }\mu\text{A}, I_B = 0$	$V_{(BR)CB0}$	300	–	–	V	
PZTA 92		–	–	–		
PZTA 93		200	–	–		
Emitter-base breakdown voltage $I_E = 100\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EB0}$	5	–	–	V	
Collector-base cutoff current $V_{CB} = 200\text{ V}$	$I_{CB0}$	–	–	250		nA
PZTA 92		–	–	250		nA
$V_{CB} = 160\text{ V}$		–	–	20	$\mu\text{A}$	
PZTA 93		–	–	20	$\mu\text{A}$	
$V_{CB} = 200\text{ V}, T_A = 150\text{ °C}$		–	–	20	$\mu\text{A}$	
PZTA 92		–	–	20	$\mu\text{A}$	
$V_{CB} = 160\text{ V}, T_A = 150\text{ °C}$		–	–	20	$\mu\text{A}$	
PZTA 93		–	–	20	$\mu\text{A}$	
Emitter-base cutoff current $V_{EB} = 3\text{ V}, I_C = 0$	$I_{EB0}$	–	–	100	nA	
DC current gain <sup>1)</sup> $I_C = 1\text{ mA}, V_{CE} = 10\text{ V}$	$h_{FE}$	25	–	–	–	
$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$		40	–	–		
$I_C = 30\text{ mA}, V_{CE} = 10\text{ V}$		25	–	–		
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 20\text{ mA}, I_B = 2\text{ mA}$	$V_{CEsat}$	–	–	0.5	V	
PZTA 92		–	–	0.4		
PZTA 93		–	–	0.4		
Base-emitter saturation voltage <sup>1)</sup> $I_C = 20\text{ mA}, I_B = 2\text{ mA}$	$V_{BEsat}$	–	–	0.9		

### AC characteristics

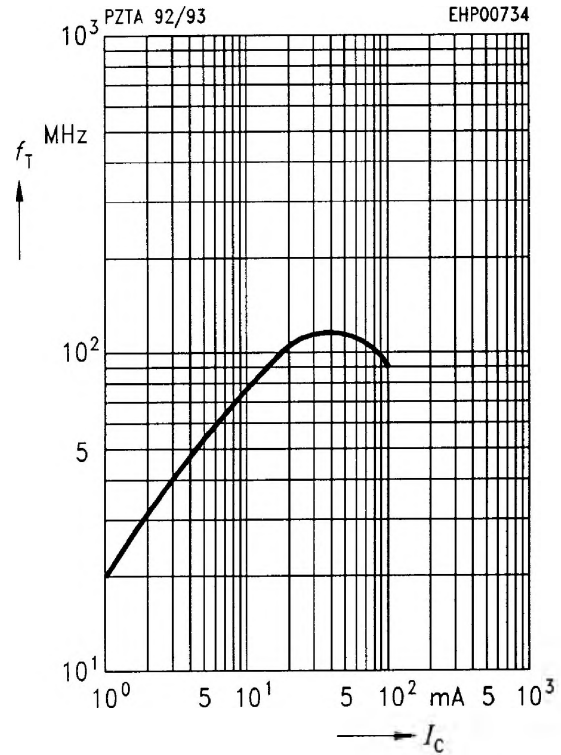
Transition frequency $I_C = 20\text{ mA}, V_{CE} = 10\text{ V}, f = 100\text{ MHz}$	$f$	–	100	–	MHz
Collector-base capacitance $V_{CB} = 20\text{ V}, f = 1\text{ MHz}$	$C_{obo}$	–	–	6	pF
PZTA 92		–	–	8	
PZTA 93		–	–	8	

<sup>1)</sup> Pulse test conditions:  $t \leq 300\text{ }\mu\text{s}, D = 2\text{ %}$ .

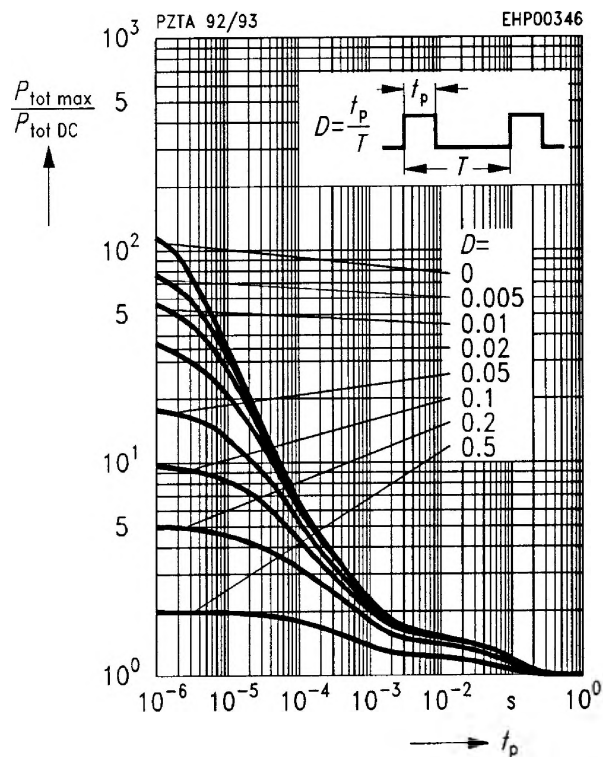
**Total power dissipation**  $P_{tot} = f(T_A^*; T_S)$   
\* Package mounted on epoxy



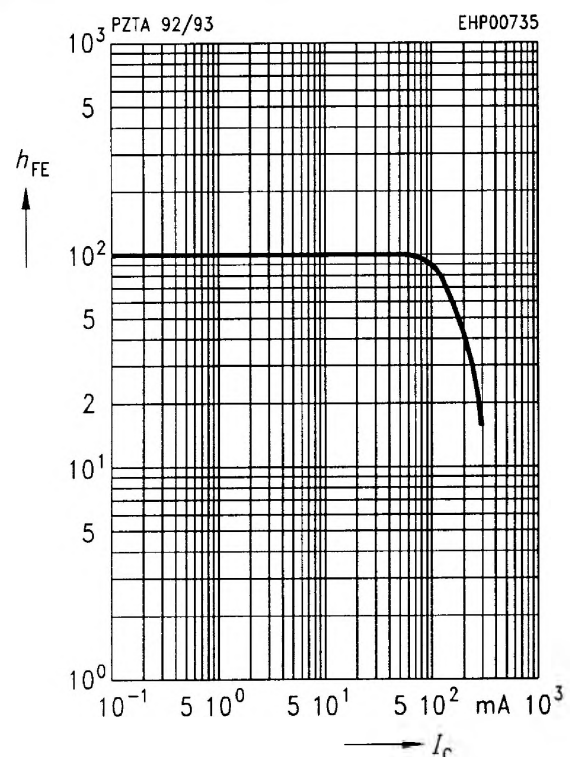
**Transition frequency**  $f_T = f(I_C)$   
 $V_{CE} = 10 V, f = 100 MHz$



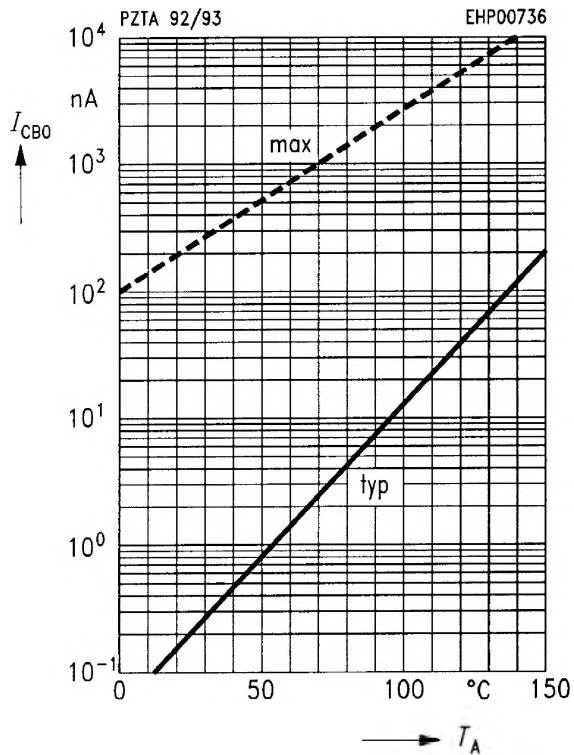
**Permissible pulse load**  $P_{tot max} / P_{tot DC} = f(t_p)$



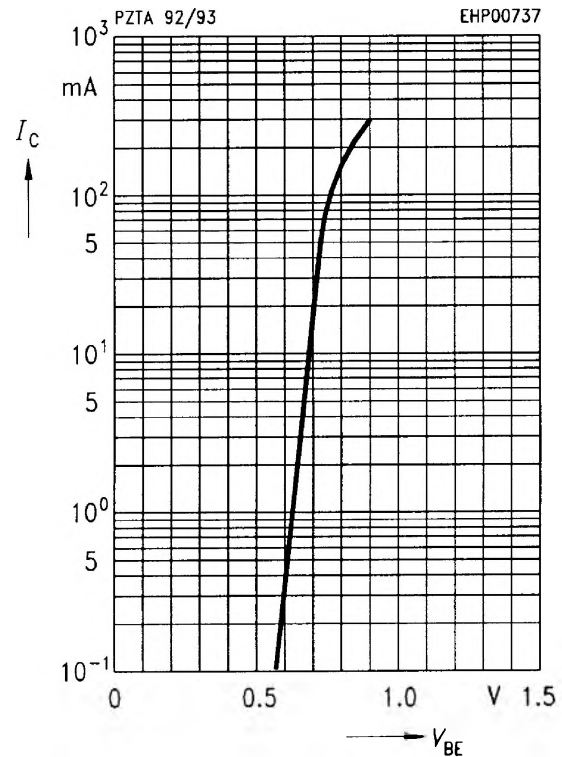
**DC current gain**  $h_{FE} = f(I_C)$   
 $V_{CE} = 10 V$



**Collector cutoff current  $I_{CB0} = f(T_A)$**   
 $V_{CB} = 160 \text{ V}$



**Collector current  $I_C = f(V_{BE})$**   
 $V_{CE} = 10 \text{ V}$



<b>SAB 80515 / 80535 Data Sheet</b>	
<b>Revision History:</b>	<b>Current Version: 08.95</b>
<b>Previous Version:</b>	<b>09.89, 11.92</b>
<b>Page</b>	<b>Subjects (changes since last revision)</b>
1, 2, 27, 29, 30	– 40 to + 110 °C version deleted; Note: only on request ... added
29	$t_C$ and $V_{int}$ ERROR modified
36	Header of table (16 MHz) corrected

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